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Docket No. 0756-2330

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#12/c  
9/19/02  
Jum

In re Patent Application of

Shunpei YAMAZAKI et al.

Serial No. 09/894,125

Filed: June 29, 2001

For: CRYSTALLINE SEMICONDUCTOR)

THIN FILM, METHOD OF FABRICATING )

THE SAME, SEMICONDUCTOR DEVICE,) )

AND METHOD OF FABRICATING THE )

SAME )

) Art Unit: 2823

) Examiner: B. Kebede

CERTIFICATE OF MAILING

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Washington, D.C. 20231, on 9/26/02

Ava M. Dixon

AMENDMENT

Honorable Commissioner of Patents

Washington, D.C. 20231

Sir:

In response to the Office Action dated April 24, 2002 please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claims 1-6, 10-12 and 19-30 as follows:

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- DI SUB
- C1
1. (Amended) A method of manufacturing a semiconductor device comprising the steps of  
forming a semiconductor film comprising silicon over a substrate;  
irradiating said semiconductor film with laser light in air for crystallizing said semiconductor film;  
removing an oxide film formed on a surface of the semiconductor film by etching after the irradiation of the laser light; and  
leveling the surface of the semiconductor film by heating after removing said oxide film.